

Thyristor \ Diode Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

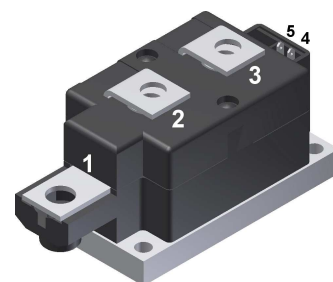
$$I_{TAV} = 220 \text{ A}$$

$$V_T = 1.18 \text{ V}$$

Phase leg

Part number

MCD225-12io1



Backside: isolated

 E72873



Features / Advantages:

- International standard package
- Direct copper bonded Al₂O₃-ceramic with copper base plate
- Planar passivated chip
- Keyed gate/cathode twin pins

Applications:

- Motor control, softstarter
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Solid state switches

Package: Y1

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.



Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1	mA
		$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			40	mA
V_T	forward voltage drop	$I_T = 200\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.04	V
		$I_T = 400\text{ A}$				0.97	V
		$I_T = 200\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.18	V
		$I_T = 400\text{ A}$				1.14	V
I_{TAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 140^{\circ}\text{C}$			220	A
$I_{T(RMS)}$	RMS forward current	180° sine				400	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}\text{C}$			0.79	V
r_T	slope resistance					0.83	mΩ
R_{thJC}	thermal resistance junction to case					0.157	K/W
R_{thCH}	thermal resistance case to heatsink				0.04		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			730	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			8.00	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			8.64	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			6.80	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			7.35	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			320.0	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			310.5	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			231.2	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			224.4	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		366		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 140^{\circ}\text{C}$			120	W
		$t_p = 500\text{ }\mu\text{s}$				60	W
P_{GAV}	average gate power dissipation					20	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 660\text{ A}$				100	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 1\text{ A}/\mu\text{s};$ $I_G = 1\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 220\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$			1000	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			2	V
			$T_{VJ} = -40^{\circ}\text{C}$			3	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
			$T_{VJ} = -40^{\circ}\text{C}$			220	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$			0.25	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	$t_p = 30\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 1\text{ A}; di_G/dt = 1\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 220\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 50\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$			200		μs

Package Y1			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal			600	A
T _{VJ}	virtual junction temperature		-40		140	°C
T _{op}	operation temperature		-40		125	°C
T _{stg}	storage temperature		-40		125	°C
Weight				680		g
M _D	mounting torque		4.5		7	Nm
M _T	terminal torque		11		13	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	16.0			mm
d _{Spb/Apb}		terminal to backside	16.0			mm
V _{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V
			50/60 Hz, RMS; I _{ISOL} ≤ 1 mA			



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

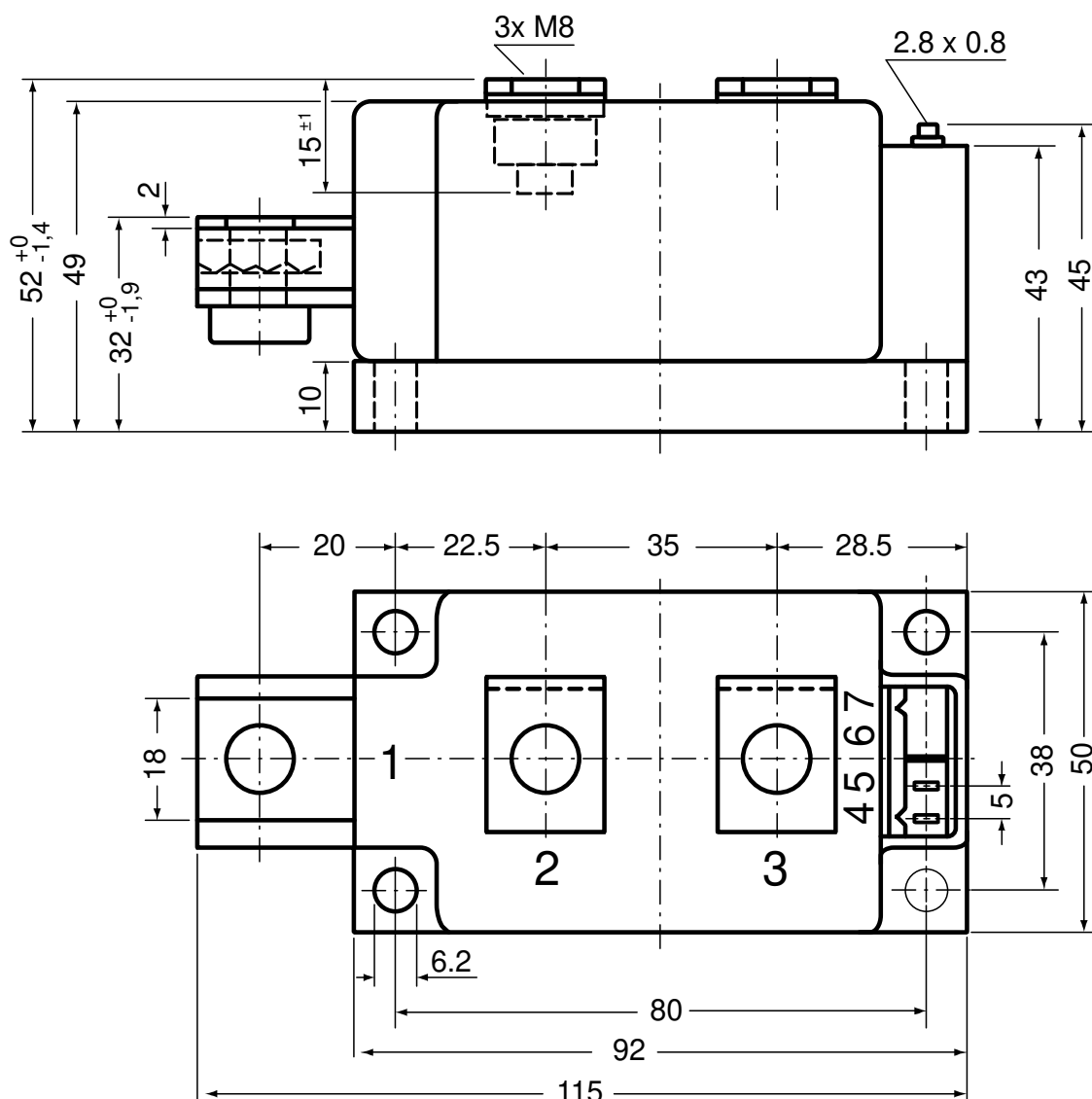
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD225-12io1	MCD225-12io1	Box	3	483966

Equivalent Circuits for Simulation

* on die level

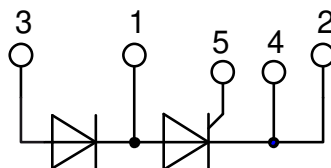
$T_{VJ} = 140^{\circ}\text{C}$

			Thyristor	
$V_{0\ max}$	threshold voltage	0.79		V
$R_{0\ max}$	slope resistance *	0.64		mΩ

Outlines Y1

Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751



Thyristor

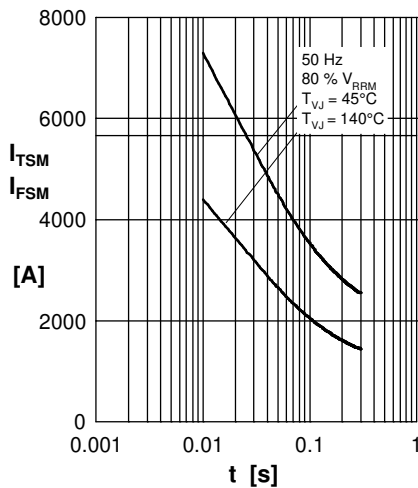


Fig. 1 Surge overload current
 $I_{TSM/FSM}$: Crest value, t : duration



Fig. 2 I^2dt versus time

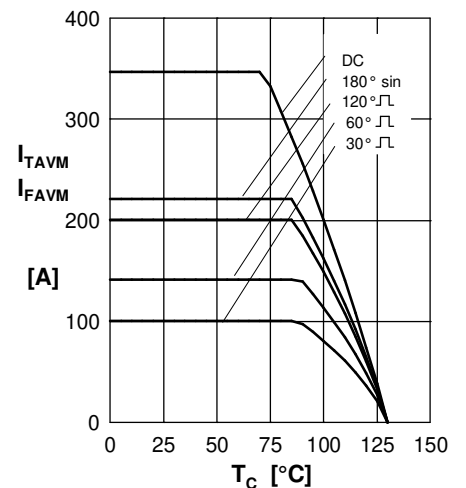


Fig. 3 Max. forward current at case temperature

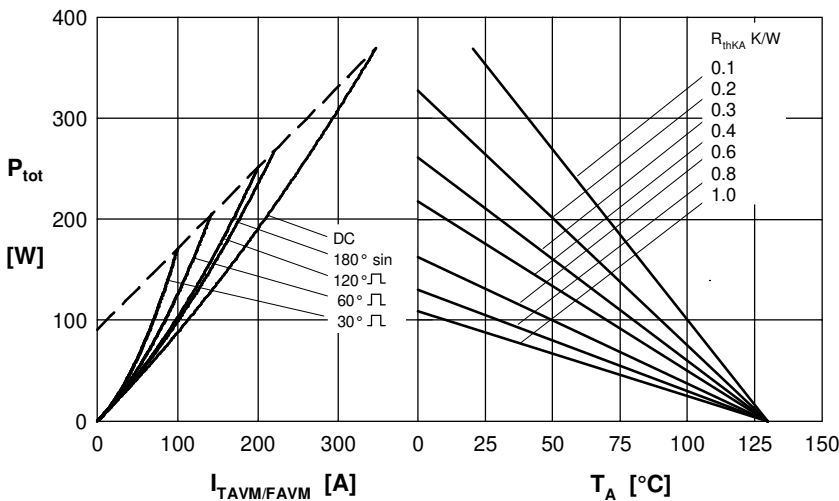


Fig. 4 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

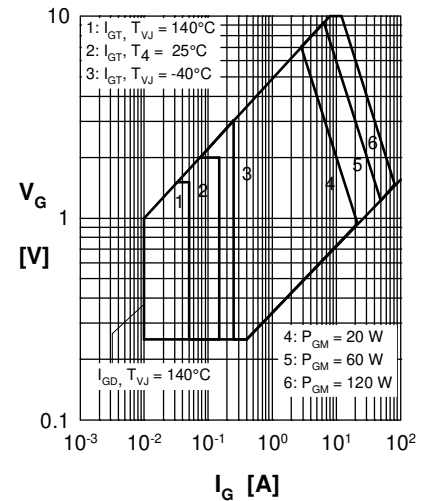


Fig. 5 Gate voltage and current

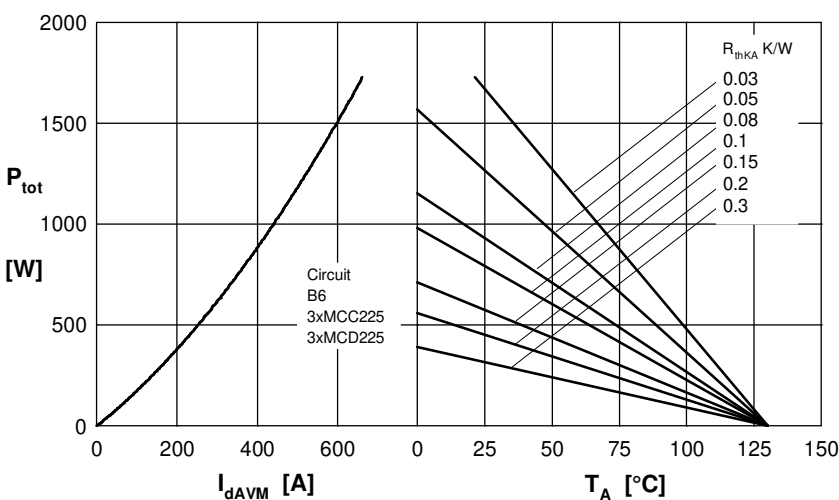


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

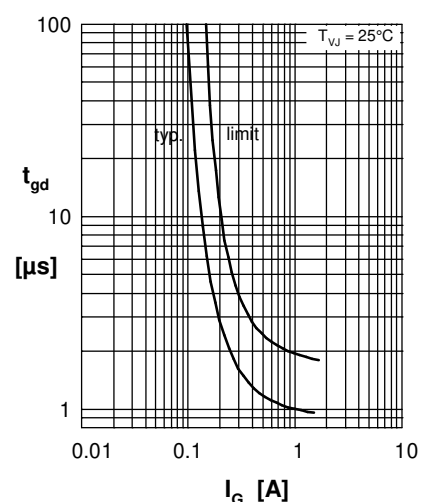


Fig. 7 Gate trigger characteristics

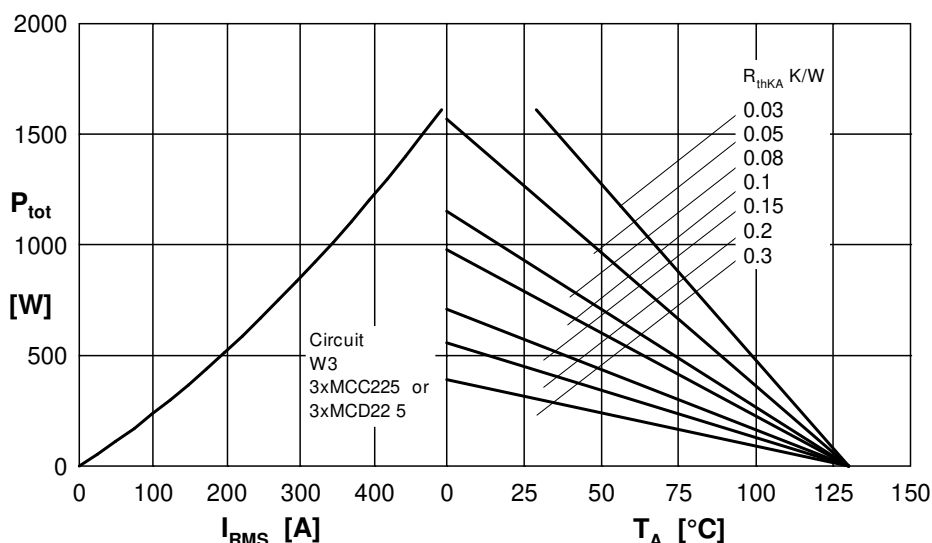
Rectifier


Fig. 8 Three phase AC-controller: Power dissipation versus R_{MS} output current and ambient temperature

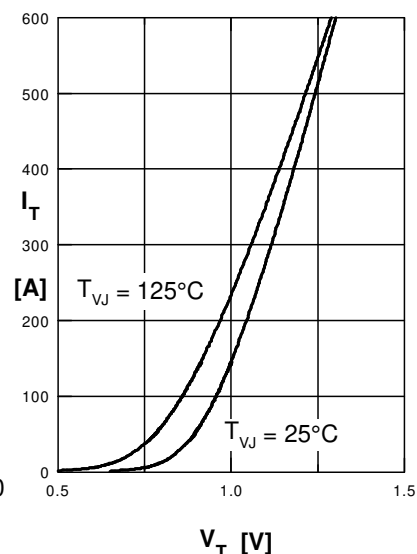


Fig. 9 Forward characteristics

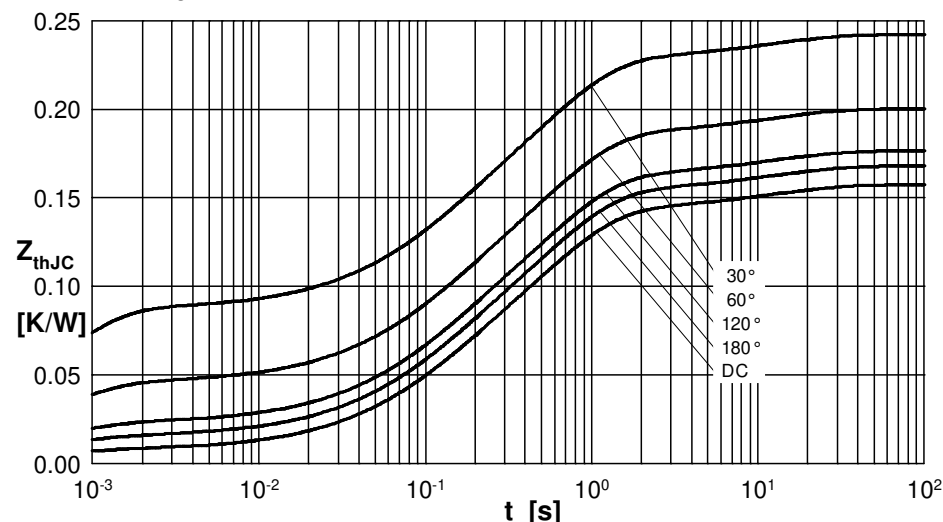


Fig. 10 Transient thermal impedance junction to case (per thyristor/diode)

R_{thJC} for various conduct. angles d:

d	R_{thJC} (K/W)
DC	0.157
180°	0.168
120°	0.177
60°	0.200
30°	0.243

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t (s)
1	0.0076	0.00054
2	0.0406	0.09800
3	0.0944	0.54000
4	0.0147	12.0000

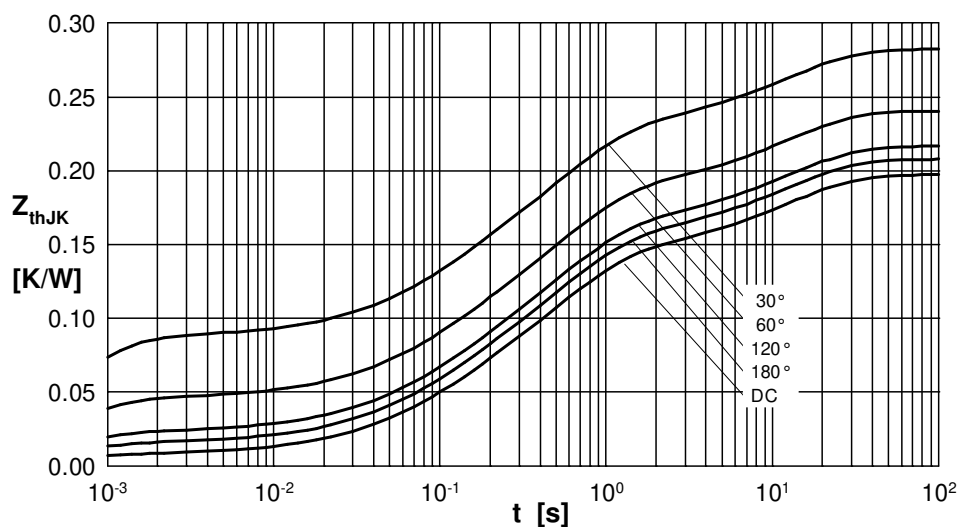


Fig. 11 Transient thermal impedance junction to heatsink (per thyristor/diode)

R_{thJK} for various conduct. angles d:

d	R_{thJK} (K/W)
DC	0.197
180°	0.208
120°	0.217
60°	0.240
30°	0.283

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t (s)
1	0.0076	0.00054
2	0.0406	0.09800
3	0.0944	0.54000
4	0.0147	12.0000
5	0.0400	12.0000